

Thierry Ouisse

List of Publications by Year in descending order

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46
papers

683
citations

840119

11
h-index

580395

25
g-index

47
all docs

47
docs citations

47
times ranked

922
citing authors

#	ARTICLE	IF	CITATIONS
1	Magnetic properties of the T_j ETQq1 1 0.784314 rgBT /Overlo xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mo>(</mml:mo><mml:msub><mml:mi>		

#	ARTICLE	IF	CITATIONS
19	Interaction between Vapor Species and Graphite Crucible during the Growth of SiC by PVT. Materials Science Forum, 2014, 778-780, 31-34.	0.3	1
20	Large Area Quasi-Free Standing Monolayer Graphene on 3C-SiC(111). Materials Science Forum, 2012, 717-720, 617-620.	0.3	4
21	Growth Rate Prediction in SiC Solution Growth Using Silicon as Solvent. Materials Science Forum, 2012, 717-720, 69-72.	0.3	2
22	Modeling of the Growth Rate during Top Seeded Solution Growth of SiC Using Pure Silicon as a Solvent. Crystal Growth and Design, 2012, 12, 909-913.	1.4	25
23	Raman scattering from Ti ₃ SiC ₂ single crystals. Applied Physics Letters, 2011, 98, 081912.	1.5	49
24	Optical Investigation of Defect Filtering Effects in Bulk 3C-SiC Crystals Grown by the CF-PVT Method Using a Necking Technique. Materials Science Forum, 2011, 679-680, 169-172.	0.3	0
25	Improvements of the Continuous Feed-Physical Vapor Transport Technique (CF-PVT) for the Seeded Growth of 3C-SiC Crystals. Materials Science Forum, 2010, 645-648, 63-66.	0.3	3
26	Heavily p-Type Doping of Bulk 6H-SiC and 3C-SiC Grown from Al-Si Melts. Materials Science Forum, 2010, 645-648, 59-62.	0.3	3
27	Dislocation-Induced Birefringence in Silicon Carbide. Materials Science Forum, 2009, 615-617, 271-274.	0.3	0
28	Conduction and Trapping in RF MEMS capacitive switches with a SiN layer. , 2009, , .		4
29	Photon Emission Analysis of Defect-Free 4H-SiC pn Diodes in Avalanche Regime. Materials Science Forum, 2002, 389-393, 1293-1296.	0.3	6
30	Hot-Carrier Luminescence in 4H-SiC MESFETs. Materials Science Forum, 2002, 389-393, 1371-1374.	0.3	0
31	Noise Behavior of 4H-SiC MESFETs at Low Drain Voltage. Materials Science Forum, 2001, 353-356, 703-706.	0.3	0
32	Properties of Transmission Lines on Various SiC Substrates. Materials Science Forum, 2000, 338-342, 1267-1270.	0.3	0
33	Neutral impurity scattering with electron screening. Physica B: Condensed Matter, 1999, 270, 262-271.	1.3	2
34	Stationary Occupied State in a Coulomb Potential with Electron Screening. Journal of the Physical Society of Japan, 1999, 68, 2150-2150.	0.7	0
35	Impact Ionization in 6H-SiC MOSFETs. Materials Science Forum, 1998, 264-268, 1009-1012.	0.3	1
36	Electrical Characterization of the AlN/Si(111) System. Materials Science Forum, 1998, 264-268, 1389-1392.	0.3	9

#	ARTICLE	IF	CITATIONS
37	Stationary Occupied State in a Coulomb Potential with Electron Screening. Journal of the Physical Society of Japan, 1998, 67, 4157-4163.	0.7	3
38	Unintentional incorporation of contaminants during chemical vapour deposition of silicon carbide. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1995, 29, 134-137.	1.7	6
39	Observation of nonstationary transport in deep submicronnâ€channel metalâ€oxideâ€semiconductor transistors with Shubnikovâ€de Haas oscillations. Journal of Applied Physics, 1994, 75, 4226-4232.	1.1	1
40	Influence of series resistances and interface coupling on the transconductance of fully-depleted silicon-on-insulator MOSFETs. Solid-State Electronics, 1992, 35, 141-149.	0.8	69
41	Study of the Spontaneous Nucleation of 3C-SiC Single Crystals Using CF-PVT Technique. Materials Science Forum, 0, 645-648, 55-58.	0.3	3
42	Identification of the Basal Plane Component of the Burgers Vector of Small Dislocations in 6H SiC Using Birefringence Microscopy. Materials Science Forum, 0, 717-720, 331-334.	0.3	0
43	Absence of Back Stress Effect in the PVT Growth of 6H Silicon Carbide. Materials Science Forum, 0, 740-742, 48-51.	0.3	0
44	Comparison of Thermodynamic Databases for the Modeling of SiC Growth by PVT. Materials Science Forum, 0, 778-780, 35-38.	0.3	1
45	Spiral Step Dissociation on PVT Grown SiC Crystals. Materials Science Forum, 0, 778-780, 39-42.	0.3	1
46	Effect of Aluminum during the High Temperature Solution Growth of Si-Face 4H-SiC. Materials Science Forum, 0, 858, 37-40.	0.3	3